



30V N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

100A

Features

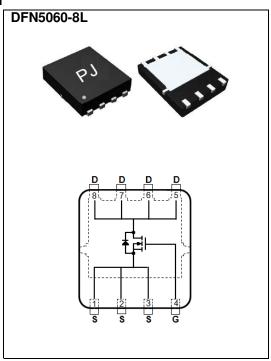
- R_{DS(ON)}, V_{GS}@10V, I_D@20A<3.8mΩ
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@15A<5.5m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060-8L Package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0028 ounces, 0.08 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBO L	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	- I _D	100		
	T _C =100°C		63	Α	
Pulsed Drain Current ^(Note 1)	T _C =25°C	I _{DM}	400		
Power Dissipation	T _C =25°C	Po	83	14/	
	T _C =100°C		33	W	
Continuous Drain Current	T _A =25°C	I _D	13.5		
	T _A =70°C		11	A	
Power Dissipation	T _A =25°C	_	2.0	14/	
Power Dissipation	T _A =70°C	Po	1.3	W	
Single Pulse Avalanche Energy ^(Note 6)		E _{AS}	100	mJ	
Operating Junction and Storage Temperature Range		T_{J},T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	1.51	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5	C/W	

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV_{DSS} $V_{GS}=0V$, $I_D=250uA$		30	-	-	. v	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1	1.6	2.5	V	
Dunin Course On State Besisters	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	2.92	3.8	mΩ	
Drain-Source On-State Resistance		V_{GS} =4.5V, I_{D} =15A	-	4.5	5.5		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	Q_g	V 45V L 04A	-	24	-	nC	
Gate-Source Charge	Q_gs	V_{DS} =15V, I_{D} =24A, V_{GS} =4.5V (Note 2,3)	-	4.2	-		
Gate-Drain Charge	Q_gd	V _{GS} =4.5V	-	13	-		
Input Capacitance	Ciss		-	2238	-		
Output Capacitance	Coss	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHZ$		272	-	pF	
Reverse Transfer Capacitance	Crss	I= I.UIVINZ	-	165	-		
Turn-On Delay Time	td _(on)	\/ 45\/ 45A	-	13	-		
Turn-On Rise Time	t _r	t_r $V_{DS}=15V, I_{D}=15A,$		20	-		
Turn-Off Delay Time	td _(off)	$V_{GS}=10V, R_{G}=1\Omega$ (Note 2,3)	-	43	-	ns	
Turn-Off Fall Time	t _f		-	13	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	ı		-	-	100	Α	
Diode Forward Current	I _S						
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	-	0.66	1	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150$ °C. Ratings are based on low frequency and duty cycles to keep initial $T_J=25$ °C.
- 4. The maximum current rating is package limited
- 5. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =45A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing





TYPICAL CHARACTERISTIC CURVES

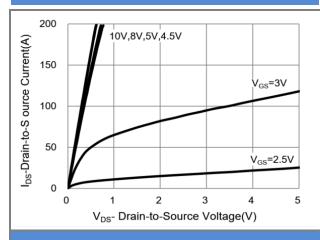


Fig.1 On-Region Characteristics

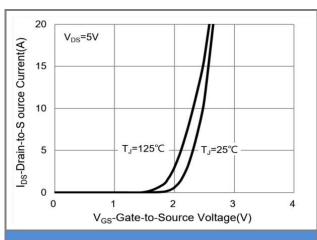


Fig.2 Transfer Characteristics

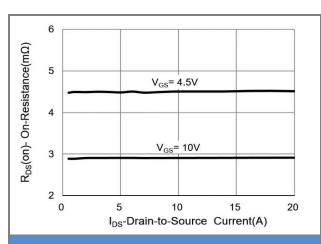


Fig.3 On-Resistance vs. Drain Current

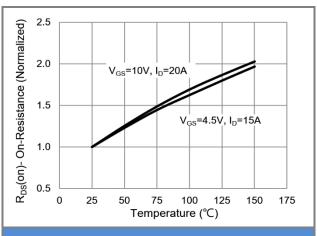
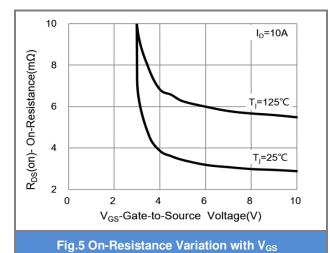
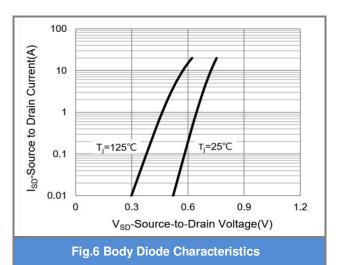


Fig.4 On-Resistance vs. Junction temperature









TYPICAL CHARACTERISTIC CURVES

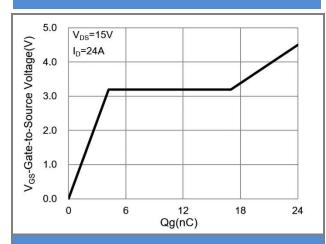


Fig.7 Gate-Charge Characteristics

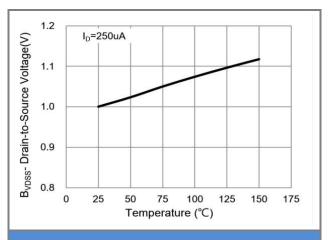


Fig.8 Breakdown Voltage Variation vs. Temperature

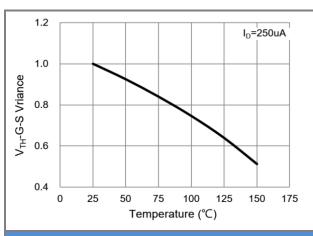


Fig.9 Threshold Voltage Variation with Temperature

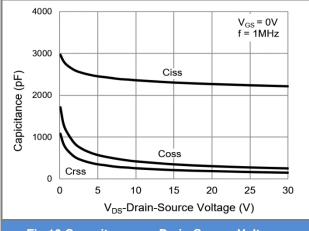


Fig.10 Capacitance vs. Drain-Source Voltage

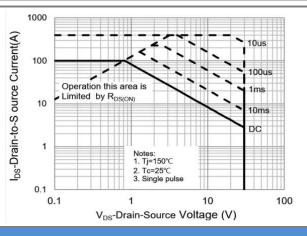


Fig.11 Maximum Safe Operating Area





TYPICAL CHARACTERISTIC CURVES

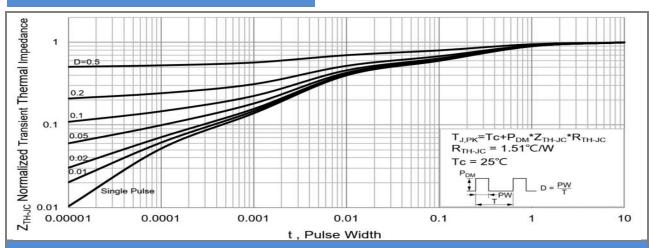


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

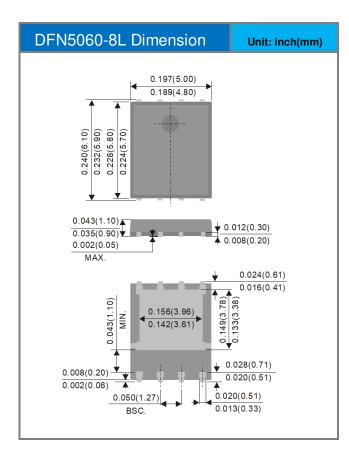


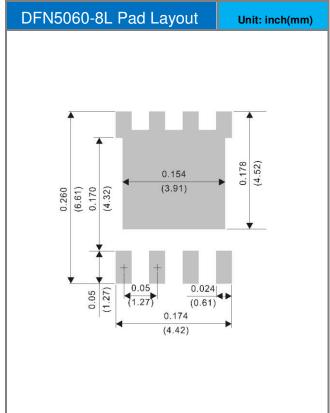


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ5424_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5424	Halogen free

Packaging Information & Mounting Pad Layout









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